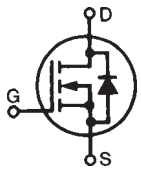
IXYS

GigaMOS™ TrenchT2 HiperFET™ Power MOSFET

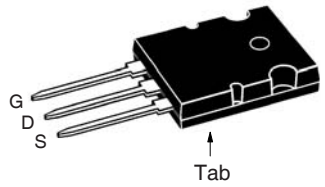
IXFK360N15T2
IXFX360N15T2

V_{DSS} = 150V
I_{D25} = 360A
$R_{DS(on)}$ ≤ 4.0mΩ
t_{rr} ≤ 150ns

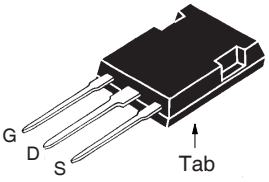
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 175°C	150	V
V_{DGR}	T_J = 25°C to 175°C, R_{GS} = 1MΩ	150	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	T_C = 25°C (Chip Capability)	360	A
$I_{L(RMS)}$	External Lead Current Limit	160	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	900	A
I_A	T_C = 25°C	100	A
E_{AS}	T_C = 25°C	TBD	J
P_D	T_C = 25°C	1670	W
dV/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 175°C$	20	V/ns
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	150			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA	2.5		5.0	V
I_{GSS}	V_{GS} = ± 20V, V_{DS} = 0V			± 200	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			50	μA
	T_J = 150°C			5	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 60A, Note 1			4.0	mΩ

Features

- International Standard Packages
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Synchronous Recification
- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

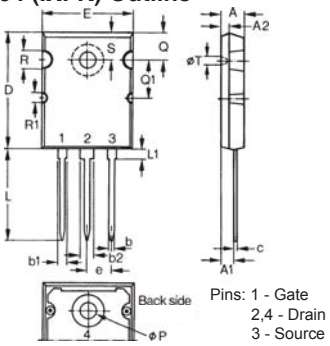
Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	140	230		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		47.5		nF
C_{oss}			3060		pF
C_{rss}			665		pF
$t_{d(on)}$	**Resistive Switching Times**		50		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 100A		170		ns
$t_{d(off)}$	R_G = 1Ω (External)		115		ns
t_f			265		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		715		nC
Q_{gs}			185		nC
Q_{gd}			200		nC
R_{thJC}				0.09	°C/W
R_{thCS}			0.15		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			360	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			1440	A
V_{SD}	I_F = 60A, V_{GS} = 0V, Note 1			1.2	V
t_{rr}	I_F = 160A, -di/dt = 100A/μs			150	ns
Q_{RM}	V_R = 60V, V_{GS} = 0V		0.50		μC
I_{RM}			9.00		A

Note 1. Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

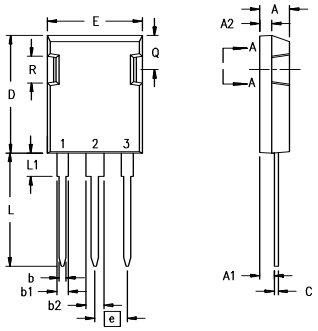
TO-264 (IXFK) Outline



Pins: 1 - Gate
2,4 - Drain
3 - Source

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS 247™ (IXFX) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ T_J = 25ºC

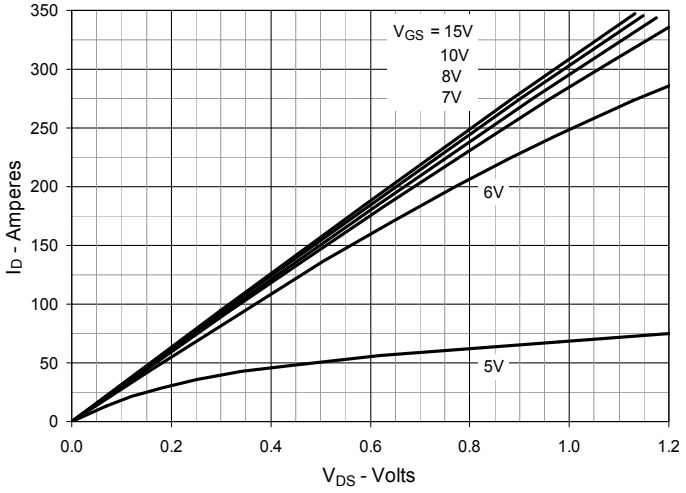


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

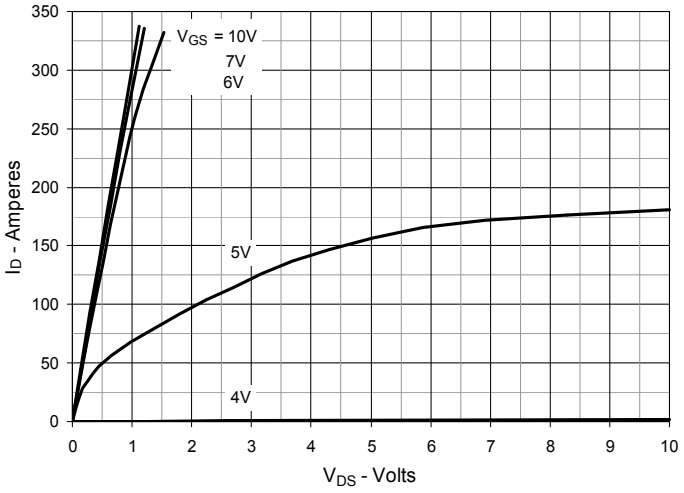


Fig. 3. Output Characteristics @ T_J = 150ºC

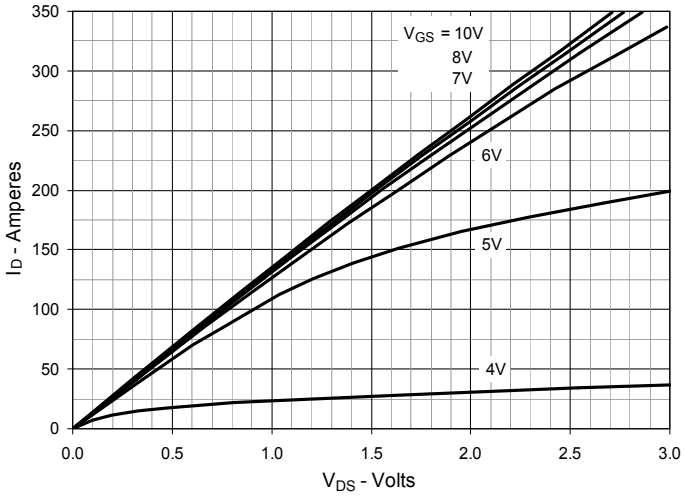


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 180A Value vs. Junction Temperature

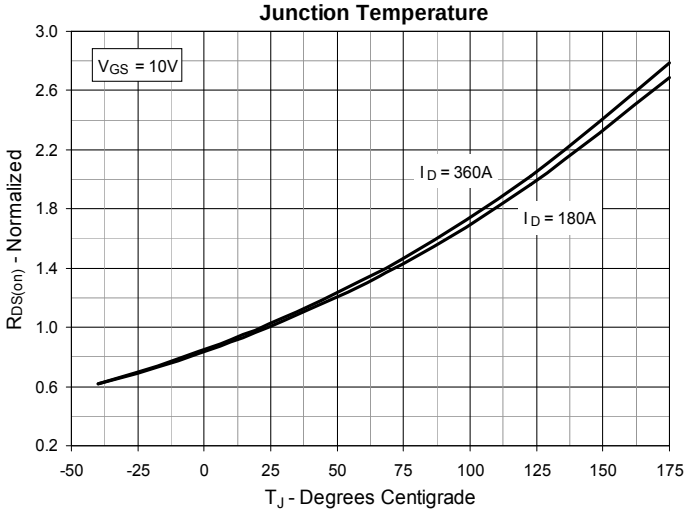


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 180A Value vs. Drain Current

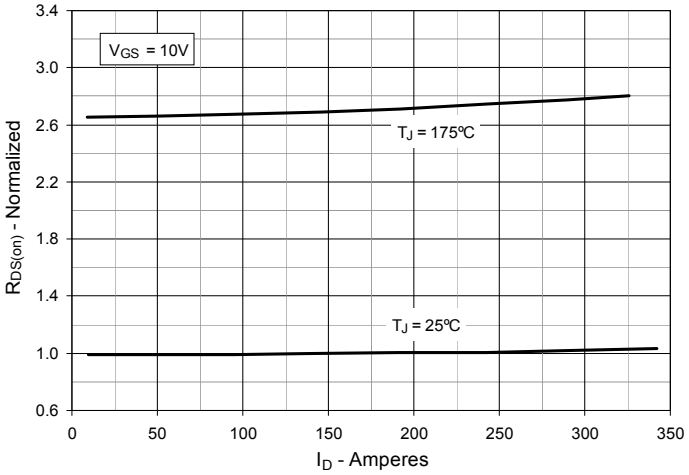


Fig. 6. Drain Current vs. Case Temperature

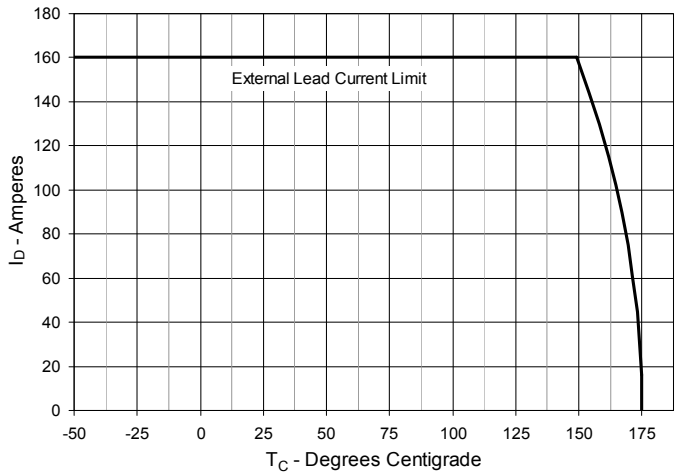


Fig. 7. Input Admittance

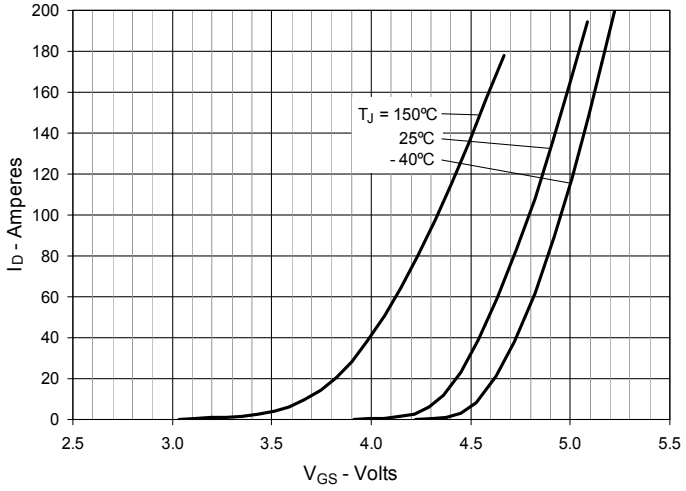


Fig. 8. Transconductance

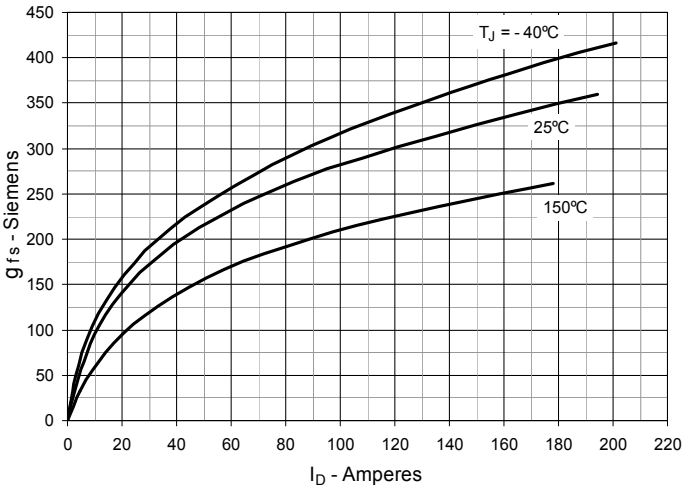


Fig. 9. Forward Voltage Drop of Intrinsic Diode

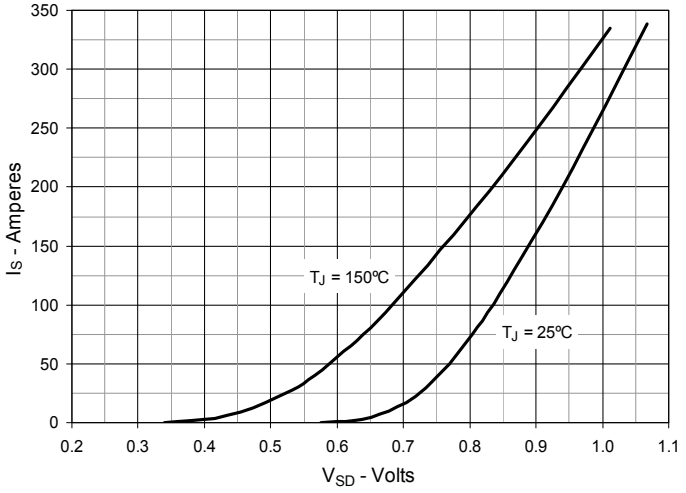


Fig. 10. Gate Charge

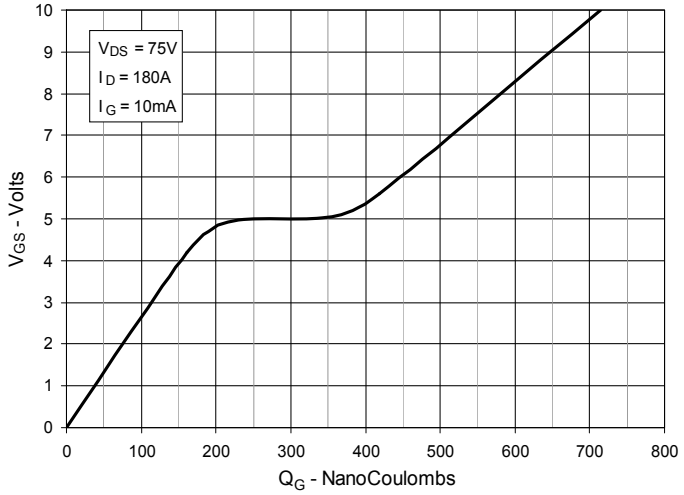


Fig. 11. Capacitance

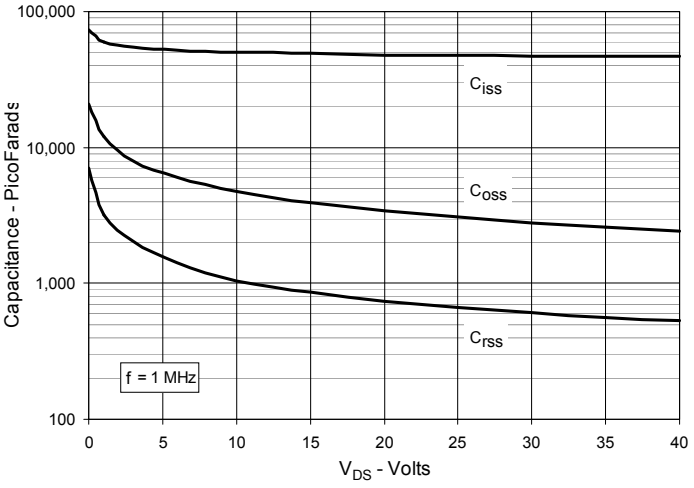


Fig. 12. Forward-Bias Safe Operating Area

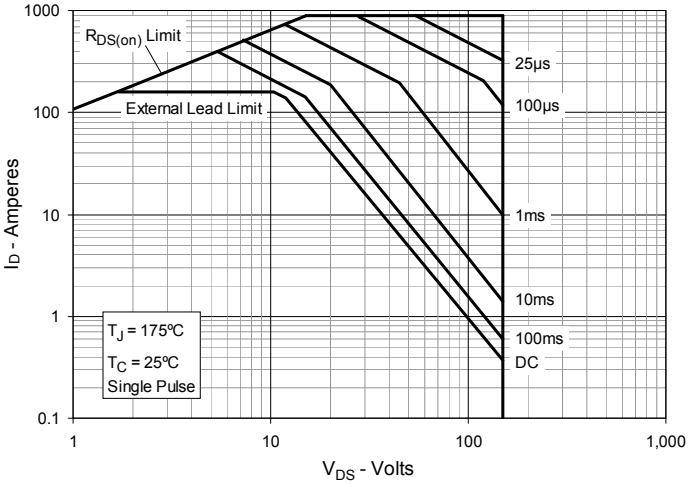


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

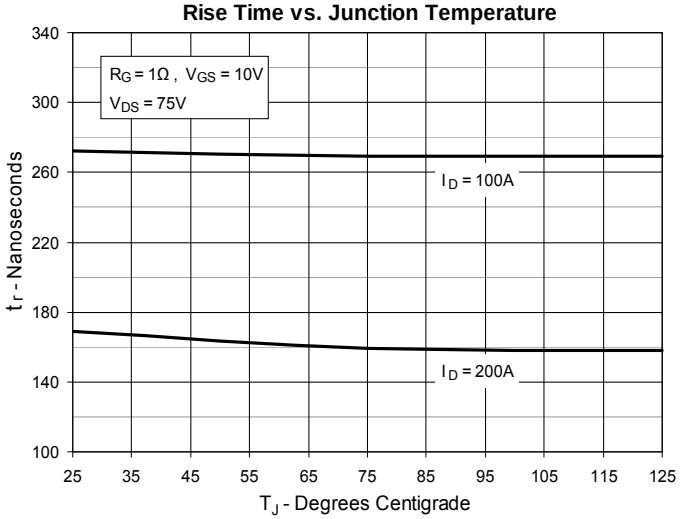


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

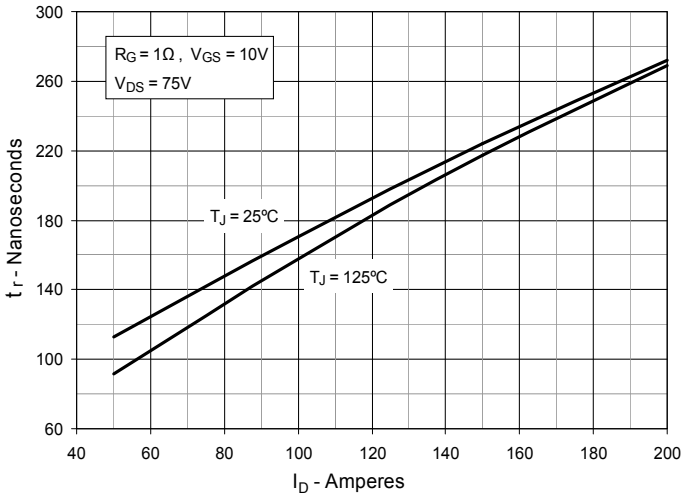


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

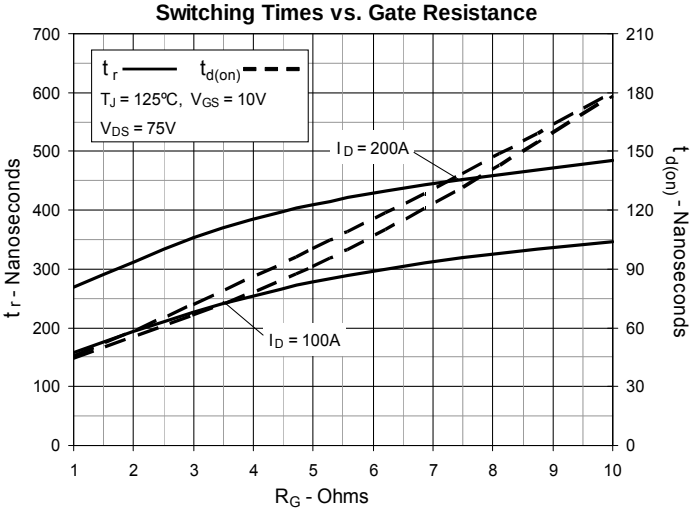


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

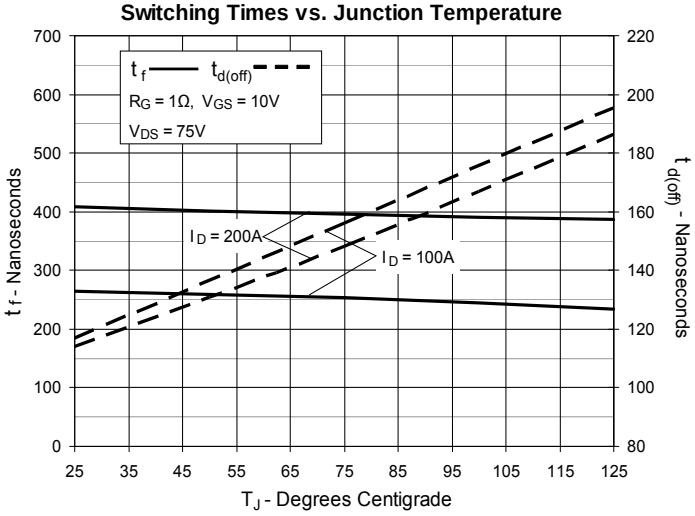


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

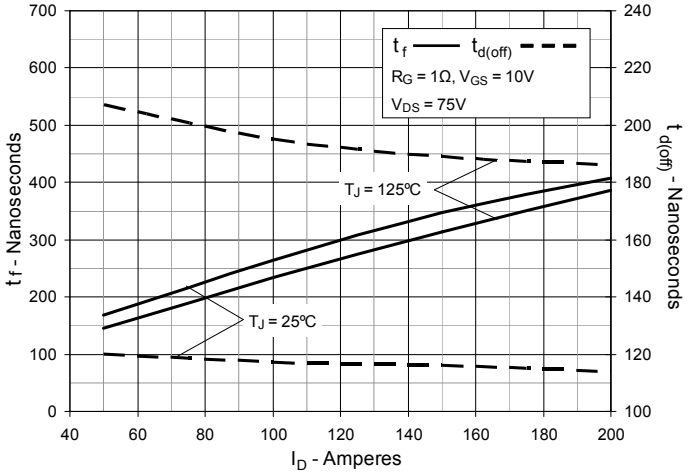


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

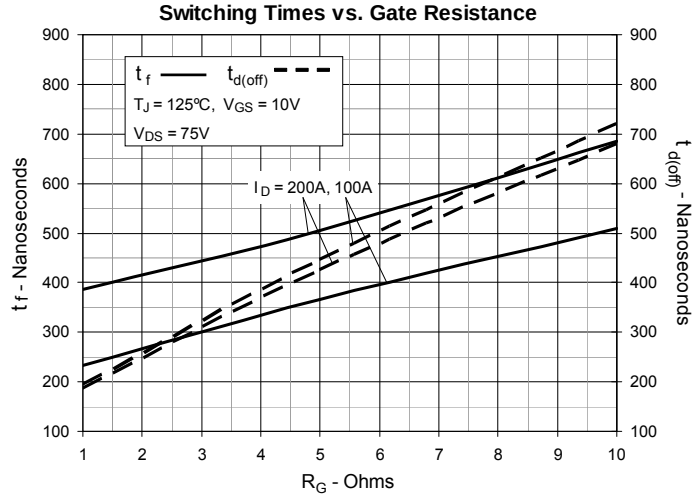


Fig. 19. Maximium Transient Thermal Impedance